

Serial No.: 09/944,506

**REMARKS**

No new matter has been added. The Applicant again requests entry of the amendments as set forth in the Appendices hereto prior to examination of the application on the merits.

Respectfully submitted,



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Enclosures: Version of Claims with Markings to Show Changes Made



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VERSION OF CLAIMS WITH MARKINGS TO SHOW CHANGES MADE

1. (Amended) A precursor to a semiconductor device structure, comprising:
  - a semiconductor device layered structure comprising a semiconductor substrate;
  - a buffer film layer located over at least a portion of said semiconductor substrate;
  - at least one trench formed in said semiconductor device layered structure; and
  - at least one shallow trench isolation structure positioned at least partially within said at least one trench and including:
    - a substantially flat surface; and
    - an integral ledge which extends laterally outward from said at least one trench so as to contact only an area of an active surface of [the]said semiconductor substrate adjacent said at least one trench.
5. (Amended) The precursor of claim 1, wherein said at least one shallow trench isolation structure comprises densified material.
11. (Amended) The intermediate semiconductor device structure of claim 7, wherein said at least one densified trench isolation structure comprises densified material.